Driver Transistor

NPN Silicon

Moisture Sensitivity Level: 1

ESD Rating: Human Body Model – 4 kV Machine Model – 400 V

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	80	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter-Base Voltage	V _{EBO}	4.0	Vdc
Collector Current – Continuous	I _C	500	mAdc

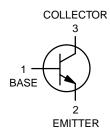
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board T _A = 25°C	P _D	150	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	833	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C



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SC-70 CASE 419 STYLE 3

MARKING DIAGRAM



GM = Specific Device Code D = Date Code

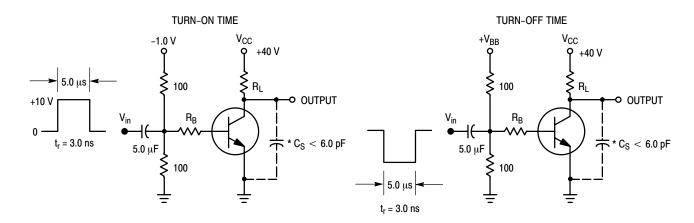
ORDERING INFORMATION

Device	Package	Shipping		
MMBTA06WT1	SC-70	3000/Tape & Reel		

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<u>.</u>			
Collector–Emitter Breakdown Voltage (Note 1) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	80	_	Vdc
Emitter–Base Breakdown Voltage ($I_E = 100 \mu Adc, I_C = 0$)	V _{(BR)EBO}	4.0	_	Vdc
Collector Cutoff Current (V _{CE} = 60 Vdc, I _B = 0)	I _{CES}	-	0.1	μAdc
Collector Cutoff Current (V _{CB} = 80 Vdc, I _E = 0)	I _{CBO}	_	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 10 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 100 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)	h _{FE}	100 100	_ _	_
Collector–Emitter Saturation Voltage (I _C = 100 mAdc, I _B = 10 mAdc)	V _{CE(sat)}	_	0.25	Vdc
Base–Emitter On Voltage (I _C = 100 mAdc, V _{CE} = 1.0 Vdc)	V _{BE(on)}	_	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS	<u>.</u>	-		•
Current–Gain – Bandwidth Product (Note 2) ($I_C = 10 \text{ mA}$, $V_{CE} = 2.0 \text{ V}$, $f = 100 \text{ MHz}$)	f _T	100	_	MHz

Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
 f_T is defined as the frequency at which |h_{fe}| extrapolates to unity.



*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

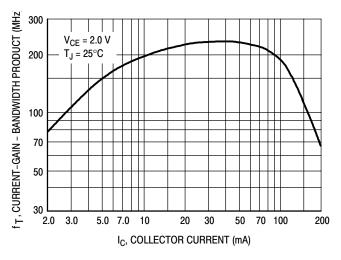


Figure 2. Current-Gain — Bandwidth Product

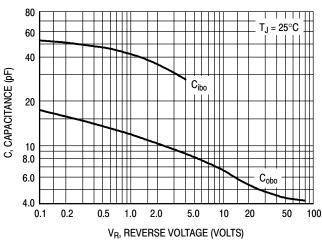


Figure 3. Capacitance

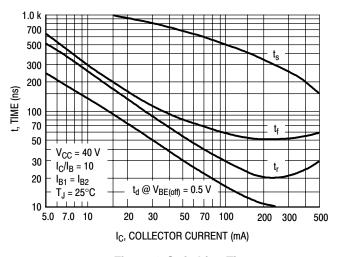


Figure 4. Switching Time

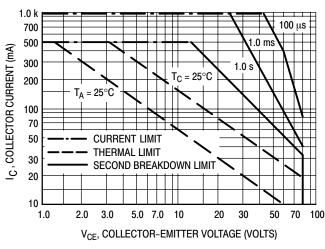


Figure 5. Active-Region Safe Operating Area

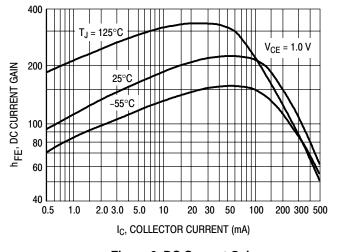


Figure 6. DC Current Gain

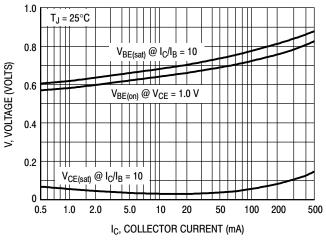
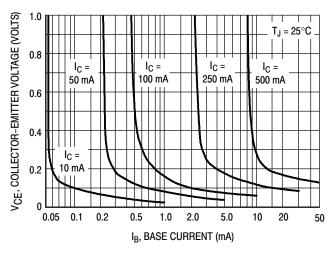


Figure 7. "ON" Voltages



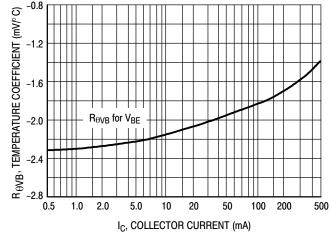
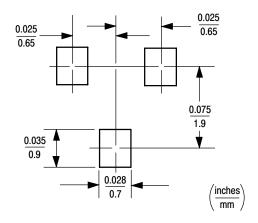


Figure 8. Collector Saturation Region

Figure 9. Base–Emitter Temperature Coefficient

INFORMATION FOR USING THE SC-70/SOT-323 SURFACE MOUNT PACKAGE MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



SC-70/SOT-323 POWER DISSIPATION

The power dissipation of the SC–70/SOT–323 is a function of the pad size. This can vary from the minimum pad size for soldering to the pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by $T_{J(max)}$, the maximum rated junction temperature of the die, $R_{\theta JA}$, the thermal resistance from the device junction to ambient; and the operating temperature, T_A . Using the values provided on the data sheet, P_D can be calculated as follows.

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature T_A of 25°C, one can calculate the power dissipation of the device which in this case is 150 milliwatts.

$$P_D = \frac{150^{\circ}C - 25^{\circ}C}{833^{\circ}C/W} = 150 \text{ milliwatts}$$

The 833°C/W assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 150 milliwatts. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad[®]. Using a board material such as Thermal Clad, a higher power dissipation can be achieved using the same footprint.

SOLDERING PRECAUTIONS

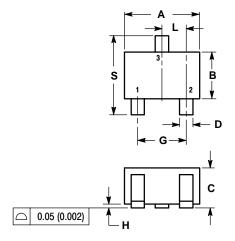
The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

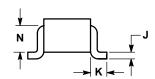
- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference should be a maximum of 10°C.

- The soldering temperature and time should not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient should be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling
- * Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

PACKAGE DIMENSIONS

SC-70/SOT-323 CASE 419-04 ISSUE L





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INCHES		INCHES MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
Н	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
S	0.079	0.095	2 00	2 40

STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR



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